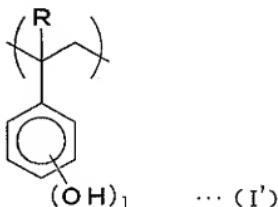


AMENDMENTS TO THE CLAIMS

1-14. (Canceled)

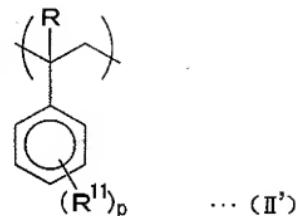
15. (Previously presented) A chemical amplification type positive photoresist composition comprising (A2) a resin made of a reaction product of (A1) an alkali soluble resin and (C1) a crosslinking polyvinyl ether compound wherein alkali solubility enhances by an action of an acid, and (B1) a photo acid generator generating acid under irradiation with radiation, wherein the component (A1) comprises a unit (a1') derived from (α -methyl)hydroxystyrene represented by the following general formula (I'):



wherein R represents a hydrogen atom or a methyl group and l represents an integer of 1 to 3, and an alkali-insoluble unit (a2') having no acid dissociable dissolution inhibiting group, and wherein a dissolution rate of the component (A1) to an aqueous 2.38% by weight solution of TMAH (tetramethylammonium hydroxide) is from 10 to 100 nm/second,

wherein the component (B1) is a poly(bissulfonyl)diazomethane photo acid generator.

16. (Original) The chemical amplification type positive photoresist composition according to claim 15, wherein the constituent unit (a2') is a unit derived from (α -methyl)styrene represented by the following general formula (II'):



wherein R represents a hydrogen atom or a methyl group, R^{11} represents an alkyl group having 1 to 5 carbon atoms and p represents an integer of 0 or 1 to 3.

17. **(Original)** The chemical amplification type positive photoresist composition according to claim 16, wherein the content of constituent unit (a2') in the component (A1) is from 5 to 35 mol%.

18. **(Original)** The chemical amplification type positive photoresist composition according to claim 15, wherein the weight-average molecular weight of the component (A2) is from 20000 to 150000.

19. **(Canceled)**

20. **(Canceled)**

21. **(Original)** The chemical amplification type positive photoresist composition according to claim 15, which further comprises a nitrogen-containing organic compound (D').

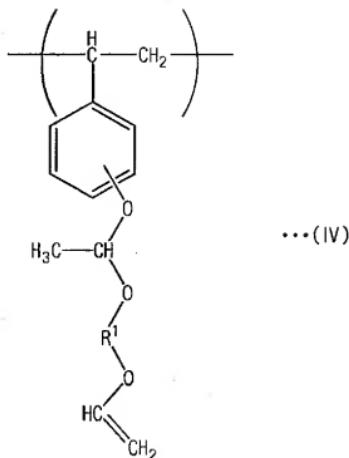
22. **(Original)** A resist pattern forming method, which comprises applying the chemical amplification type positive photoresist composition of claim 15 on a substrate, and subjecting to prebaking, selective exposure, PEB (post exposure bake) and alkali development to form a resist pattern.

23-29. **(Canceled)**

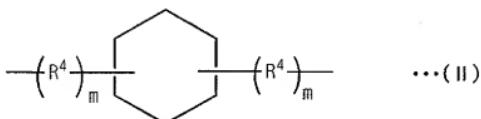
30. **(Previously presented)** A method for formation of a resist pattern of a thick-film photolithography process, which comprises forming a resist film having a thickness of 2 to 7 μm

made of a chemical amplification type positive resist composition on a substrate, wherein said chemical amplification type positive photoresist composition is prepared by dissolving:

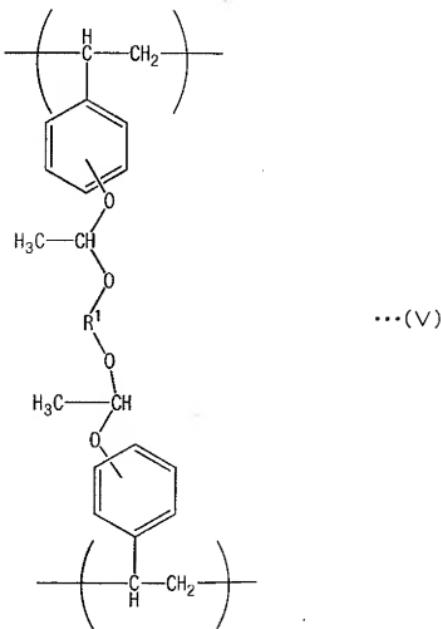
(A') a slightly alkali-soluble or alkali-insoluble polyhydroxystyrenic resin having a property that solubility in an aqueous alkali solution is enhanced in the presence of an acid, comprising either or both or a constituent unit (a'1) represented by the following general formula (IV):



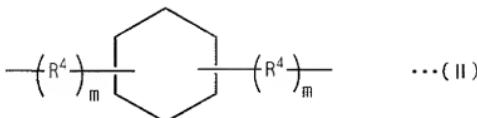
wherein R¹ represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the following general formula (II):



(wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have a oxygen bond (ether bond) in the main chain, and an intermolecular crosslinked moiety ($a'2$) represented by the following general formula (V):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the following general formula (II):



(wherein R⁴ represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain; and

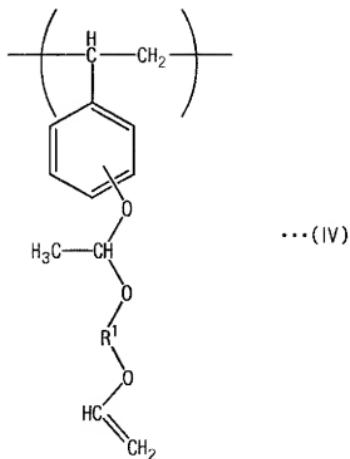
(B) a poly(bissulfonyl)diazomethane photoacid generator in an organic solvent, wherein the content of an acid component in the entire photoresist composition is 10 ppm or less; and subjecting to selective exposure, post exposure bake (PEB) treatment, and development.

31. **(Previously presented)** The method for formation of a resist pattern according to claim 30, wherein a resist pattern for implantation is formed in the thick-film photolithography process.

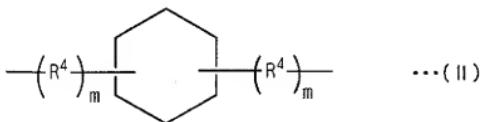
32-38. **(Canceled)**

39. **(Previously presented)** A method for formation of a resist pattern of a thick-film photolithography process, which comprises forming a resist film having a thickness of 2 to 7 μm made of a chemical amplification type positive resist composition on a substrate, wherein said chemical amplification type positive photoresist composition is prepared by dissolving:

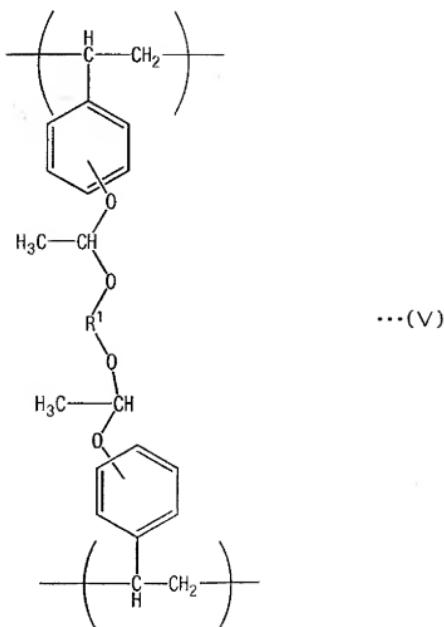
(A'') a slightly alkali-soluble or alkali-insoluble polyhydroxystyrenic resin having such a property that solubility in an aqueous alkali solution is enhanced in the presence of an acid comprising either or both of a constituent unit (a'1) represented by the following general formula (IV):



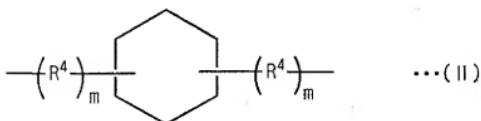
wherein R¹ represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the following general formula (II):



(wherein R⁴ represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, and an intermolecular crosslinked moiety (a'2) represented by the following general formula (V):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the following general formula (II):



(wherein R⁴ represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, and a styrenic constituent unit; and

(B) a poly(bissulfonyl)diazomethane photoacid generator in an organic solvent, wherein the content of an acid component in the entire photoresist composition is 10 ppm or less; and subjecting to selective exposure, post exposure bake (PEB) treatment, and development.

40. (Previously presented) The method for formation of a resist pattern according to claim 39, wherein a resist pattern for implantation is formed in the thick-film photolithography process.

41-43. (Canceled)